

Thermal and Electrical Properties of Rare-Earth Sulfides At High Temperatures

G.G. Gadzhiev, Sh.M. Ismailov, M.M. Khamidov, and Kh.Kh. Abdullaev

Institute of Physics

Daghestan Science Center of Russian Academy of Sciences

Jaragskogo 94

367003, Makhachkala, Russia

In the past few years there has been renewed interest in the semiconducting rare-earth sulfides (Ln_3S_4 , Ln_2S_3) (Ln, Pr, Nd, Gd, Dy), with the Th_3P_4 -type structure (defective structure - $\text{Ln}_{3-x}\text{V}_x\text{S}_4$ where V_x is the rare-earth's vacancies at cationic sublattice). The high melting points ($T > 2100$ K), low thermal conductivity ($1.5\text{--}3.5 \text{ W}\cdot\text{m}^{-1} \text{ K}^{-1}$) and the electrical conductivity changing continually from a metallic conductivity to a semiconductor with an increase in the number of vacancies V_x make them good candidates as potential high-temperature thermoelectric materials. The results of our investigations of the temperature dependence (300–1200 K) of the thermal and electrical conductivity (λ , σ), the thermal expansion coefficient and heat capacity (α , C_p) of the rare-earth sulfides $\text{Ln}_{3-x}\text{S}_4$ (Ln, Pr, Gd, Dy) ($x=0; 0.209; 0.232; 0.26; 0.28; 0.33$) are presented. The temperature dependence of the lattice (λ_L) and electronic (λ_e) contributions to the total thermal conductivity are determined. The total thermal resistivity is $W=W_1+W_2+W_3$. W_1 is the thermal resistivity caused by phonon-phonon scattering, W_2 is the thermal resistivity caused by scattering on the vacancies; and W_3 is the scattering on mass defect and change of elastic parameters. W_1 and W_2 are independent of temperature. The temperature dependence of the lattice thermal conductivity of the investigated compounds is described by an equation $\lambda \sim T^{-n}$ ($n=0.95\text{--}0.5$).

The lattice thermal conductivity from $\text{Ln}_{3-x}\text{S}_4$ to $\text{Dy}_{3-x}\text{S}_4$ is decreased. It is caused by the increase of the atomic weight and additional increase of the anharmonicity of thermal oscillations of a lattice. It is confirmed also by the dependence of the thermal expansion coefficient on composition that increases from $\text{Ln}_{3-x}\text{S}_4$ to $\text{Dy}_{3-x}\text{S}_4$ with a decrease of the sound velocity. The accuracy correlation between the lattice thermal conductivity and the thermal expansion coefficient for all compounds are observed. The electrical resistivity may be described as $\rho(T)=\rho_0+\rho_1(T)$ where ρ_0 is the resistivity caused by scattering of electrons on the cationic vacancies and ρ_1 is caused by scattering on the thermal oscillations of the lattice.